BLF571

HF / VHF power LDMOS transistor

Rev. 02 — 24 February 2009 Product data sheet

1. Product profile

1.1 General description

A 20 W LDMOS RF transistor for broadcast applications and industrial applications in the HF and VHF band.

Table 1. Production test performance

Mode of operation	f (MHz)	V_{DS} (V)	P_L (W)	G_p (dB)	η_D (%)
CW	225	50	20	27.5	70

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

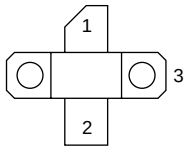
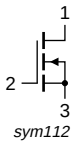
- Typical CW performance at frequency of 225 MHz, a supply voltage of 50 V and an I_{Dq} of 50 mA:
  - Average output power = 20 W
  - Power gain = 27.5 dB
  - Efficiency = 70 %
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (10 MHz to 500 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain		
2	gate		
3	source [1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF571	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT467C

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	110	V
V_{GS}	gate-source voltage		–0.5	+11	V
I_D	drain current		-	3.6	A
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 20 W	2.9	K/W

6. Characteristics

Table 6. DC characteristics

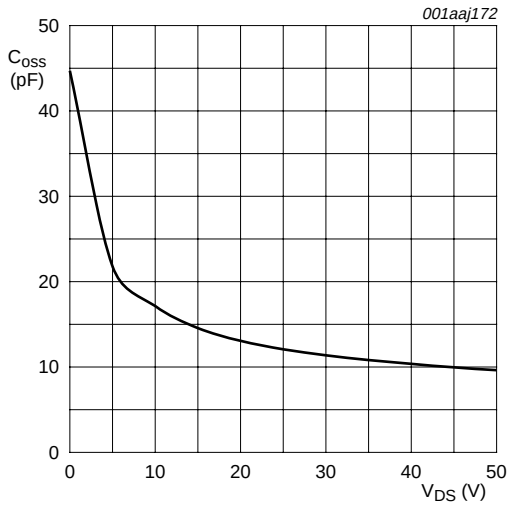
T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.25 mA	110	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 25 mA	1.25	1.7	2.25	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 50 V; I_D = 50 mA	1.25	1.75	2.25	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 50 V	-	-	1.4	µA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	3.0	3.6	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 1.25 A	-	1.8	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 833 mA	-	1.34	-	Ω
C_{rs}	feedback capacitance	V_{GS} = 0 V; V_{DS} = 50 V; f = 1 MHz	-	0.18	-	pF
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 50 V; f = 1 MHz	-	22.9	-	pF
C_{oss}	output capacitance	V_{GS} = 0 V; V_{DS} = 50 V; f = 1 MHz	-	9.64	-	pF

Table 7. RF characteristics

Mode of operation: CW; f = 225 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 50 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	P_L = 20 W	25.5	27.5	29.5	dB
RL_{in}	input return loss	P_L = 20 W	10	13	-	dB
η_D	drain efficiency	P_L = 20 W	67	70	-	%



V_{GS} = 0 V; f = 1 MHz.

Fig 1. Output capacitance as a function of drain-source voltage; capacitance value without internal matching

6.1 Ruggedness in class-AB operation

The BLF571 is capable of withstanding a load mismatch corresponding to VSWR = 13 : 1 through all phases under the following conditions: V_{DS} = 50 V; I_{Dq} = 50 mA; P_L = 20 W; f = 225 MHz.

7. Application information

7.1 Impedance information

Table 8. Typical impedance

Simulated Z_S and Z_L test circuit impedances.

f	Z_S	Z_L
MHz	Ω	Ω
225	9.7 + j31.5	31.7 + j29.3

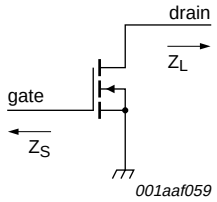
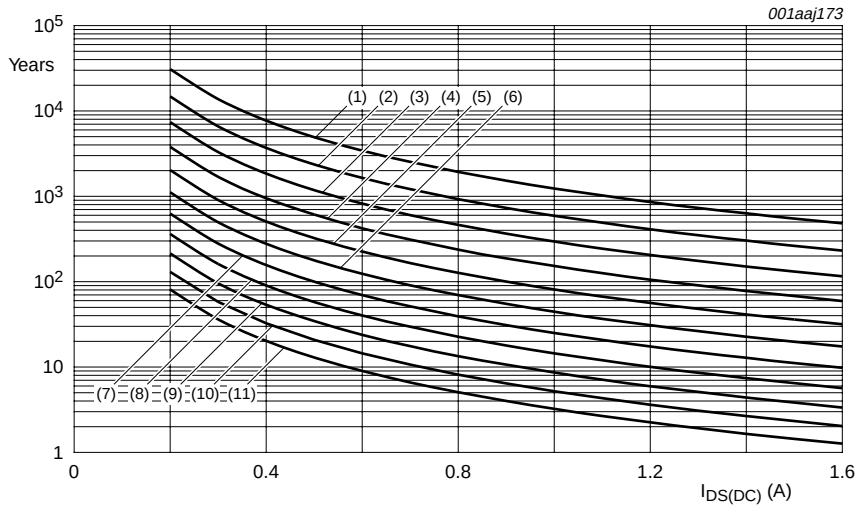


Fig 2. Definition of transistor impedance

7.2 Reliability



TTF (0.1 % failure fraction).

(1) T_j = 100 °C
(2) T_j = 110 °C
(3) T_j = 120 °C
(4) T_j = 130 °C
(5) T_j = 140 °C
(6) T_j = 150 °C
(7) T_j = 160 °C
(8) T_j = 170 °C
(9) T_j = 180 °C
(10) T_j = 190 °C
(11) T_j = 200 °C

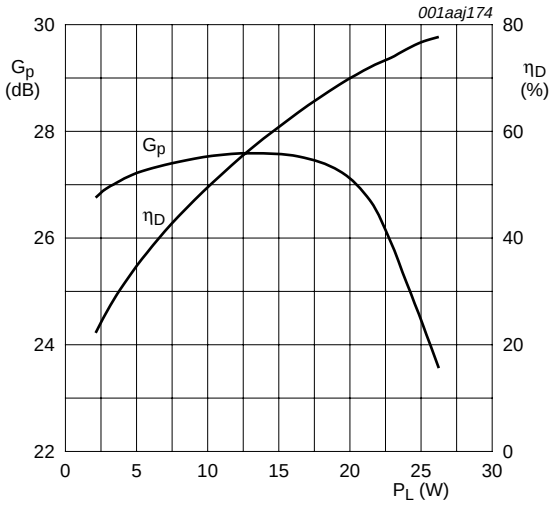
Fig 3. BLF571 electromigration

8. Test information

8.1 RF performance

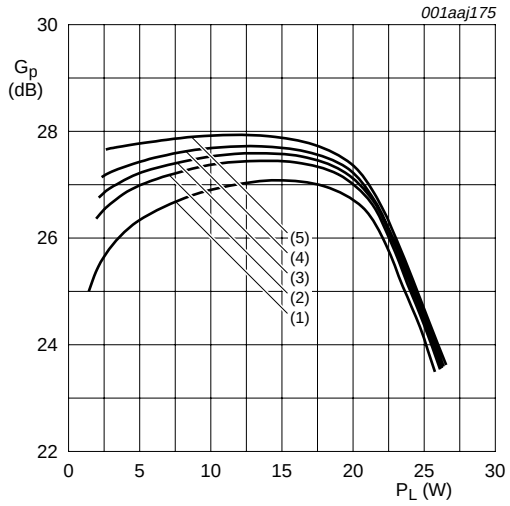
The following figures are measured in a class-AB production test circuit.

8.1.1 1-Tone CW



V_{DS} = 50 V; I_{Dq} = 50 mA; f = 225 MHz.

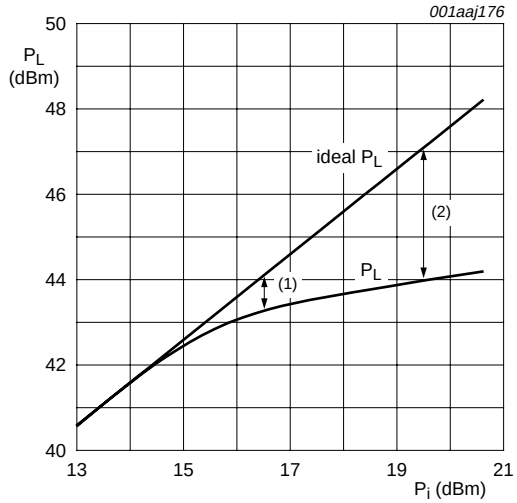
Fig 4. Power gain and drain efficiency as function of load power; typical values



V_{DS} = 50 V; f = 225 MHz.

(1) I_{Dq} = 20 mA
(2) I_{Dq} = 40 mA
(3) I_{Dq} = 50 mA
(4) I_{Dq} = 60 mA
(5) I_{Dq} = 80 mA

Fig 5. Power gain as a function of load power; typical values



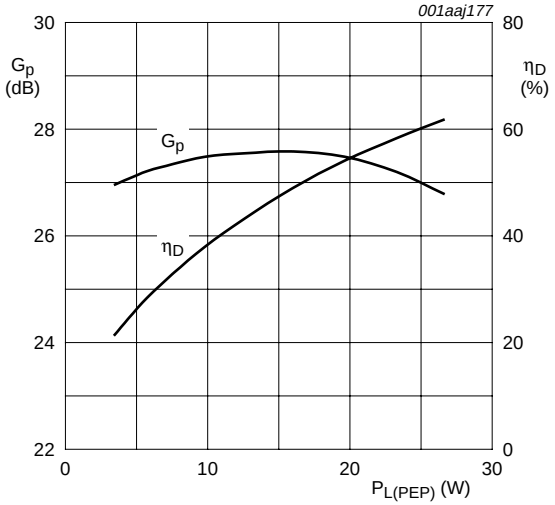
V_{DS} = 50 V; I_{Dq} = 50 mA; f = 225 MHz.

(1) $P_{L(1dB)}$ = 43.3 dBm (21.4 W)

(2) $P_{L(3dB)}$ = 44 dBm (25.1 W)

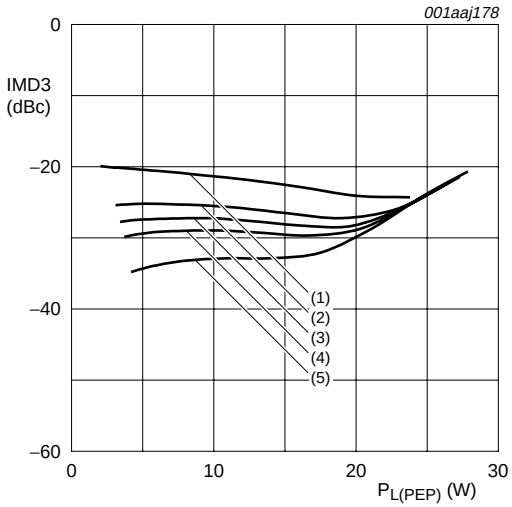
Fig 6. Load power as function of input power; typical values

8.1.2 2-Tone CW



V_{DS} = 50 V; I_{Dq} = 50 mA; f_1 = 224.95 MHz; f_2 = 225.05 MHz.

Fig 7. Power gain and drain efficiency as function of peak envelope load power; typical values



V_{DS} = 50 V; f_1 = 224.95 MHz; f_2 = 225.05 MHz.

(1) I_{Dq} = 20 mA

(2) I_{Dq} = 40 mA

(3) I_{Dq} = 50 mA

(4) I_{Dq} = 60 mA

(5) I_{Dq} = 80 mA

Fig 8. Third order intermodulation distortion as a function of peak envelope load power; typical values

8.2 Test circuit

Table 9. List of components

All capacitors should be soldered vertically. For test circuit, see Figure 9 and Figure 10.

Component	Description	Value		Remarks
C1, C3, C4, C5, C14	multilayer ceramic chip capacitor	100 pF	[1]	
C2	multilayer ceramic chip capacitor	39 pF	[1]	
C6	multilayer ceramic chip capacitor	68 pF	[1]	
C7, C9	multilayer ceramic chip capacitor	1 nF	[1]	
C8	multilayer ceramic chip capacitor	4.7 µF		TDK C4532X7R1E475MT020U or equivalent
C10	multilayer ceramic chip capacitor	8.2 pF	[1]	
C11	electrolytic capacitor	220 µF		
C12	multilayer ceramic chip capacitor	33 pF	[1]	
C13	multilayer ceramic chip capacitor	15 pF	[1]	
L1	1 turn enamelled copper wire	D = 5.5 mm; d = 1 mm; length = 1 mm		
L2	2 turns enamelled copper wire	D = 3.5 mm; d = 1 mm; length = 3 mm		
L3	5 turns enamelled copper wire	D = 6 mm; d = 1 mm; length = 5 mm		
L4	3.3 turns enamelled copper wire	D = 3 mm; d = 1 mm; length = 4 mm		
L5	3 turns enamelled copper wire	D = 3 mm; d = 1 mm; length = 3 mm		
L6	stripline	-	[2]	(L × W) 16.5 mm × 2.4 mm
L7, L8, L10, L11, L17, L19, L20	stripline	-	[2]	(L × W) 3.0 mm × 5.0 mm
L9	stripline	-	[2]	(L × W) 43.0 mm × 2.4 mm
L12, L15	stripline	-	[2]	(L × W) 3.5 mm × 2.4 mm
L13, L14	stripline	-	[2]	(L × W) 8.0 mm × 8.0 mm
L16	stripline	-	[2]	(L × W) 3.0 mm × 5.9 mm
L18	stripline	-	[2]	(L × W) 27.0 mm × 2.4 mm
L21	stripline	-	[2]	(L × W) 28.5 mm × 2.4 mm
R1	metal film resistor	1000 Ω; 0.6 W		

[1] American Technical Ceramics type 100B or capacitor of same quality.

[2] Printed-Circuit Board (PCB): Rogers 5880; ε_r = 2.2 F/m; height = 0.79 mm; Cu (top/bottom metallization); thickness copper plating = 35 µm.

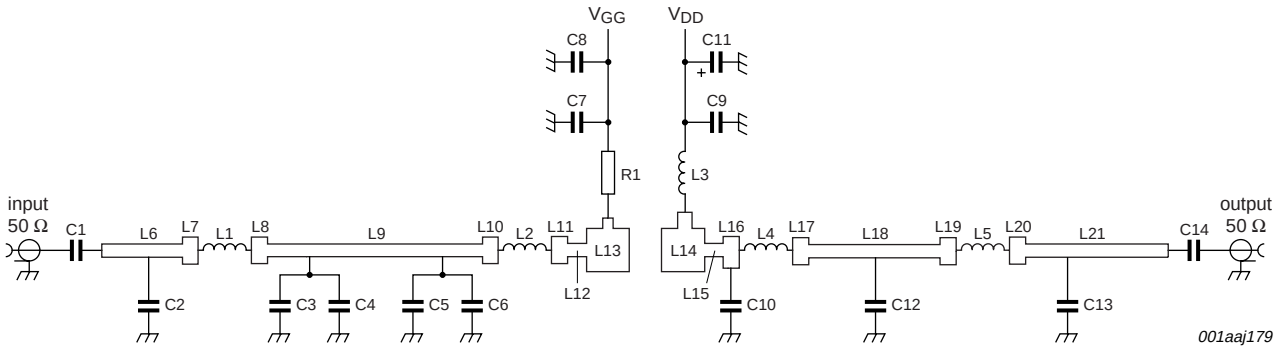


Fig 9. Class-AB common-source production test circuit

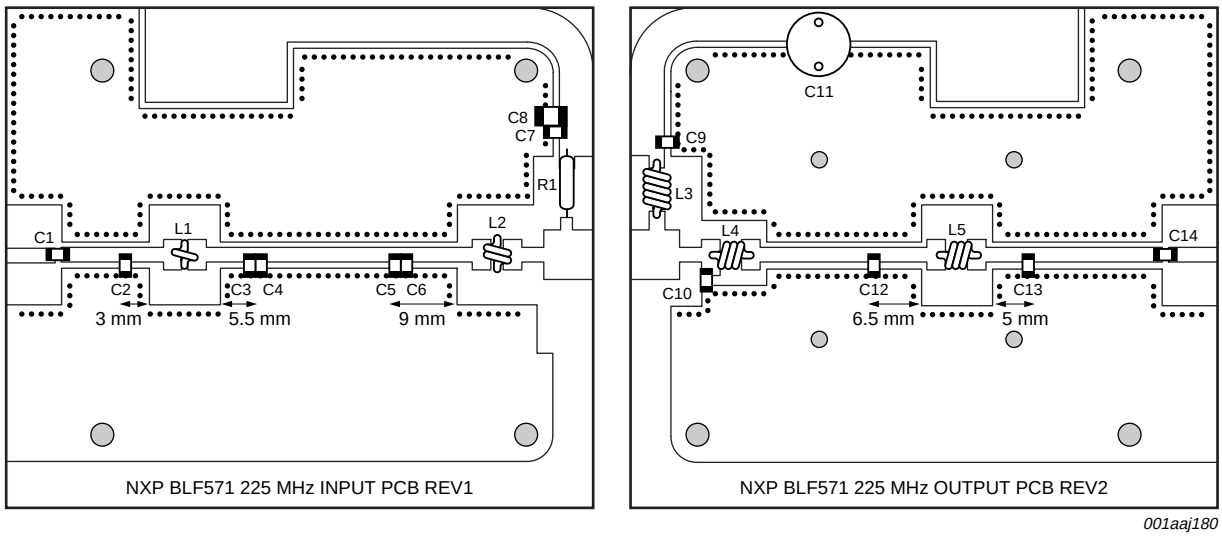
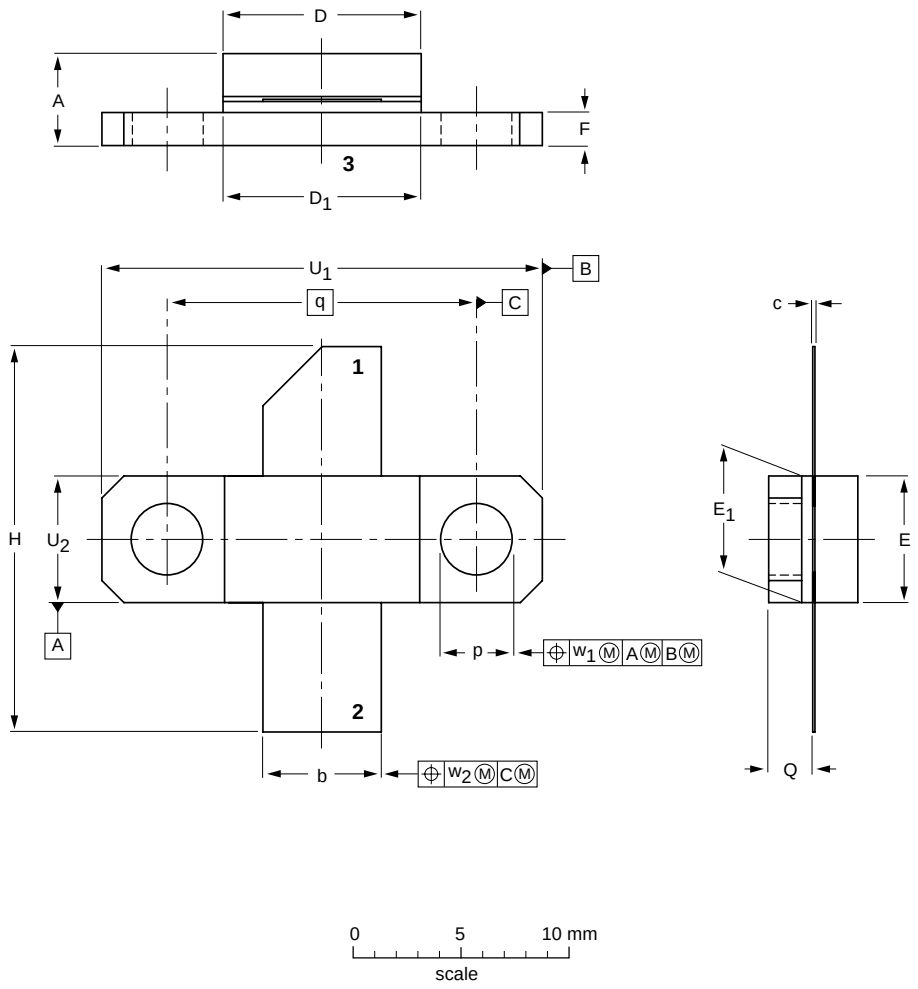


Fig 10. Component layout for class-AB production test circuit

9. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads **SOT467C**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D_1	E	E_1	F	H	p	Q	q	U_1	U_2	w_1	w_2
mm	4.67 3.94	5.59 5.33	0.15 0.10	9.25 9.04	9.27 9.02	5.92 5.77	5.97 5.72	1.65 1.40	18.54 17.02	3.43 3.18	2.21 1.96	14.27	20.45 20.19	5.97 5.72	0.25	0.51
inch	0.184 0.155	0.220 0.210	0.006 0.004	0.364 0.356	0.365 0.355	0.233 0.227	0.235 0.225	0.065 0.055	0.73 0.67	0.135 0.125	0.087 0.077	0.562	0.805 0.795	0.235 0.225	0.010	0.020

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT467C						~~99-12-06~~ 99-12-28

Fig 11. Package outline SOT467C

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
CW	Continuous Wave
EDGE	Enhanced Data rates for GSM Evolution
GSM	Global System for Mobile communications
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
RF	Radio Frequency
TTF	Time To Failure
VHF	Very High Frequency
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF571_2	20090224	Product data sheet	-	BLF571_1
Modifications:	• Data sheet status updated from Preliminary to Product			
BLF571_1	20081211	Preliminary data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

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Date of release: 24 February 2009
Document identifier: BLF571_2